IN THE CLAIMS:

Please amend claim 1 and 6 as follows:

1. (Currently Amended) A semiconductor device comprising:

a semiconductor substrate;

two adjacent semiconductor components provided on the principal surface of the substrate; ~~and~~

multiple through holes, which pass from the principal surface through the backside of the substrate and are provided in a region of the substrate ~~between~~ sandwiched by the two adjacent semiconductor components so as to substantially eliminate the electrical interference between the two adjacent semiconductor components; and

a conductor film formed directly on the side faces of the through holes.

2. (Original) The device of Claim 1, wherein a gap between two adjacent ones of the through holes is smaller than the thickness of the substrate.

3. (Cancelled)

4. (Previously Presented) The device of Claim 1, further comprising a grounded wiring layer provided on the backside of the substrate,

wherein the conductor film is connected to the grounded wiring layer.

5. (Original) The device of Claim 1, wherein each of the components is a power-amplifying transistor for a radio frequency signal.

6. (Currently Amended) A semiconductor device comprising:

a semiconductor substrate;

at least two semiconductor components provided on the principal surface of the substrate;

electrodes of the at least two components provided on the substrate;

a first group of through holes, which pass from the principal surface through the backside of the substrate and are provided in respective regions of the substrate under the electrodes;

a first conductor film provided on the side faces of the first group of through holes;

a second group of through holes, which pass from the principal surface through the backside of the substrate and are provided in a region of the substrate between the components;

a second conductor film provided on the side faces of the second group of through holes; and

a wiring layer, which is provided on the backside of the substrate and is in contact with the first and second conductor films;

wherein the second group of through holes are provided in different locations from the first group of through holes.

7. (Original) The device of Claim 6, wherein each of the components is a power-amplifying transistor for an RF signal.

8. (Previously Presented) The device of Claim 1, where in the multiple through holes stand in a line.

9. (Previously Presented) A semiconductor device comprising:

a semiconductor substrate;

at least two semiconductor components provided on the principal surface of the substrate;

multiple through holes, which pass from the principal surface through the backside of the substrate and are provided in a region of the substrate between at least the two components so as to substantially eliminate the electrical interference between at least the two semiconductor components; and

a conductor film formed directly on the side faces of the through holes.

10. (Previously Presented) The device of claim 9 further comprising a grounded wiring layer provided on the backside of the substrate,

wherein the conductor film is connected to the grounded wiring layer.